

Features

- Split Gate Trench MOSFET Technology
- Excellent Package for Heat Dissipation
- High Density Cell Design for Low $R_{DS(ON)}$
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)
- Moisture Sensitivity Level 1

Maximum Ratings

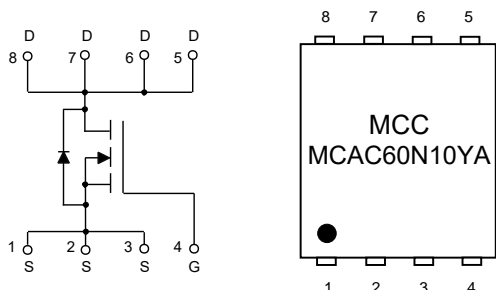
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 20°C/W Junction to Ambient($t < 10s$)⁽²⁾
- Thermal Resistance: 50°C/W Junction to Ambient(Steady-State)⁽²⁾
- Thermal Resistance: 1.42°C/W Junction to Case(Steady-State)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	60	A
Pulsed Drain Current ⁽³⁾	I_{DM}	240	A
Total Power Dissipation ⁽⁴⁾	P_D	88	W
Single Pulsed Avalanche Energy ⁽⁵⁾	E_{AS}	200	mJ

Note:

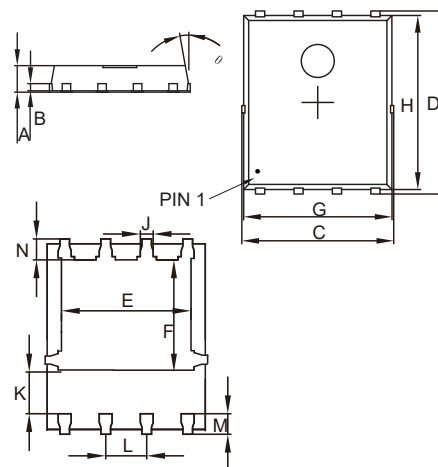
1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ C$. The Power dissipation P_{DSM} is based on $R_{\theta JA} t \leq 10s$ and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_d is based on max. junction temperature, using junction-case thermal resistance.
5. $V_{DD}=50V$, $R_G=25\Omega$, $L=1mH$, $I_{AS}=20A$.

Internal Structure and Marking Code



N-CHANNEL MOSFET

DFN5060



DIM	DIMENSIONS				NOTE
	INCHES		MM		
	MIN	MAX	MIN	MAX	
A	0.031	0.047	0.80	1.20	
B	0.010		0.254		TYP.
C	0.193	0.222	4.90	5.64	
D	0.232	0.250	5.90	6.35	
E	0.148	0.167	3.75	4.25	
F	0.126	0.154	3.20	3.92	
G	0.189	0.213	4.80	5.40	
H	0.222	0.239	5.65	6.06	
K	0.045	0.059	1.15	1.50	
J	0.012	0.020	0.30	0.50	
L	0.046	0.054	1.17	1.37	
M	0.012	0.028	0.30	0.71	
N	0.016	0.028	0.40	0.71	

Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	100			V
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.3	1.8	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$		7.5	8.6	m Ω
		$V_{GS}=4.5V, I_D=20A$		9.5	13	m Ω
Gate Resistance	R_G	f=1MHz, Open drain		0.68		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				60	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=20A$			1.3	V
Reverse Recovery Time	t_{rr}	$I_F=20A, dI_F/dt=100A/\mu s$		51.5		ns
Reverse Recovery Charge	Q_{rr}			64		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V, f=1MHz$		2270		pF
Output Capacitance	C_{oss}			797		
Reverse Transfer Capacitance	C_{riss}			36		
Total Gate Charge	Q_g	$V_{DS}=50V, V_{GS}=10V, I_D=25A$		40		nC
Gate-Source Charge	Q_{gs}			8.5		
Gate-Drain Charge	Q_{gd}			5		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=50V, V_{GEN}=10V, R_G=2.2\Omega, I_{DS}=25A$		9.3		ns
Turn-On Rise Time	t_r			34.8		
Turn-Off Delay Time	$t_{d(off)}$			24.6		
Turn-Off Fall Time	t_f			71		

Curve Characteristics

Fig. 1 - Typical Output Characteristics

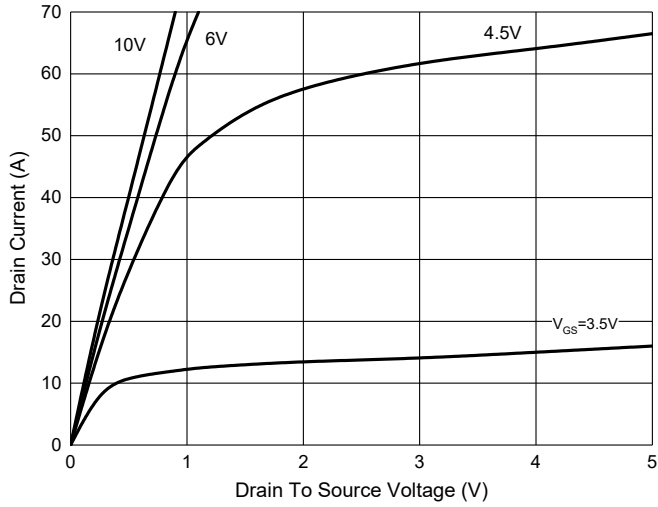


Fig. 2 - Transfer Characteristics

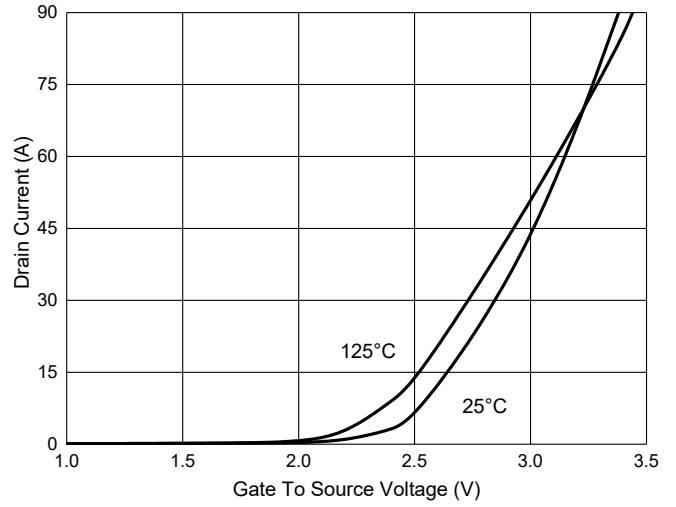


Fig. 3 - $R_{DS(ON)} - I_D$

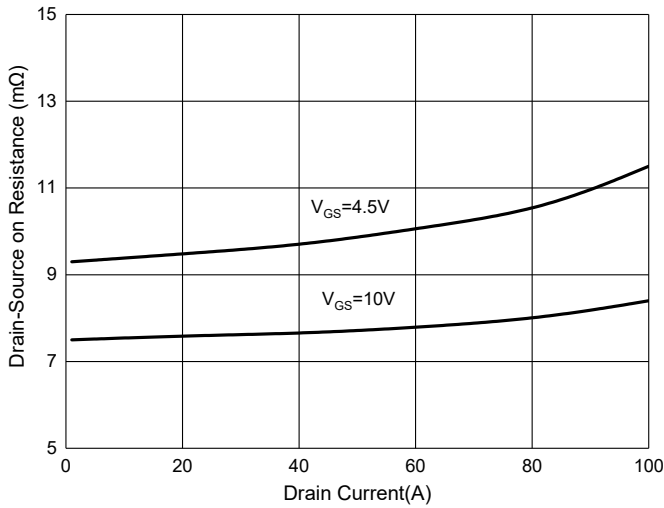


Fig. 4 - Normalized On Resistance Characteristics

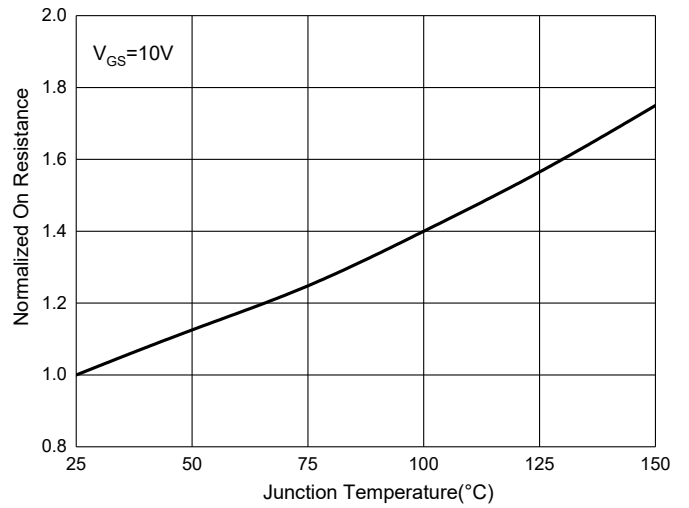


Fig. 5 - Capacitance Characteristics

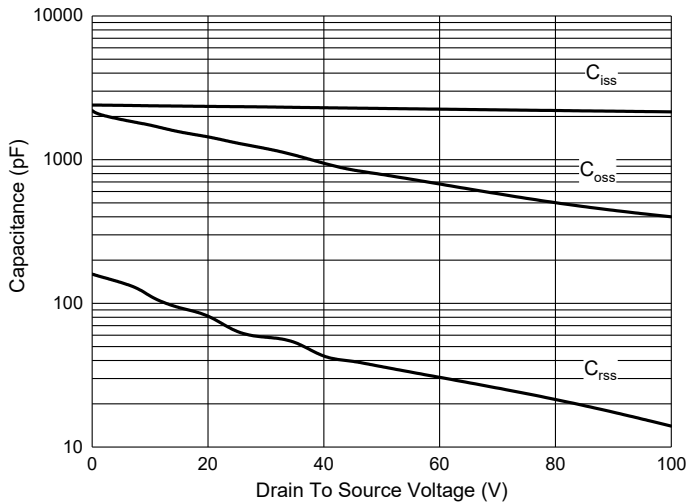
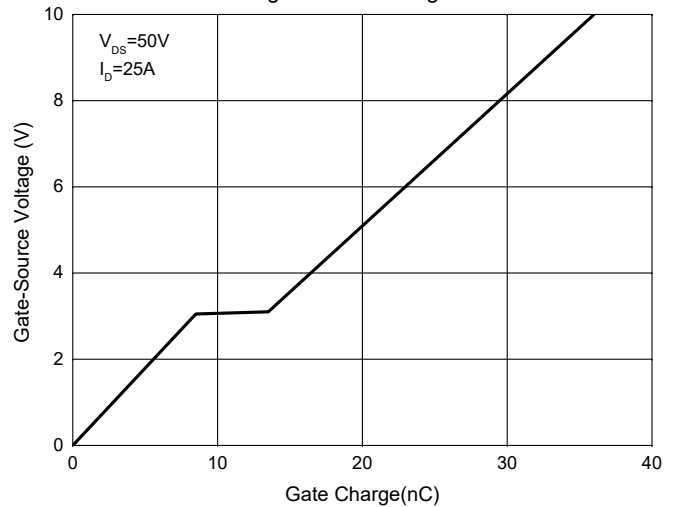


Fig. 6 - Gate Charge



Curve Characteristics

Fig. 7 - Safe Operation Area

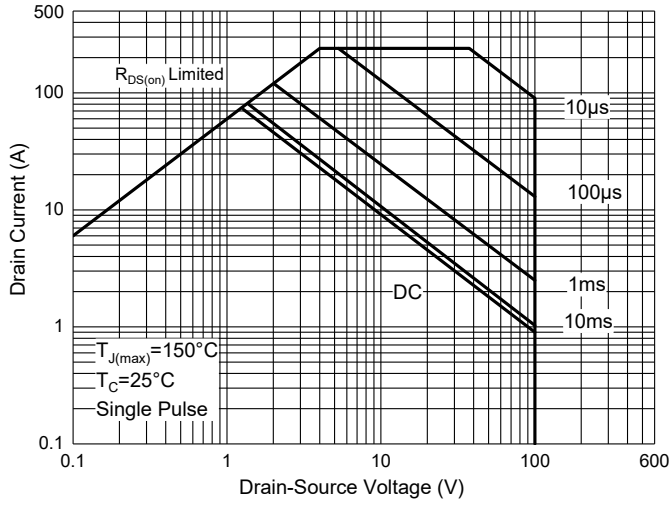
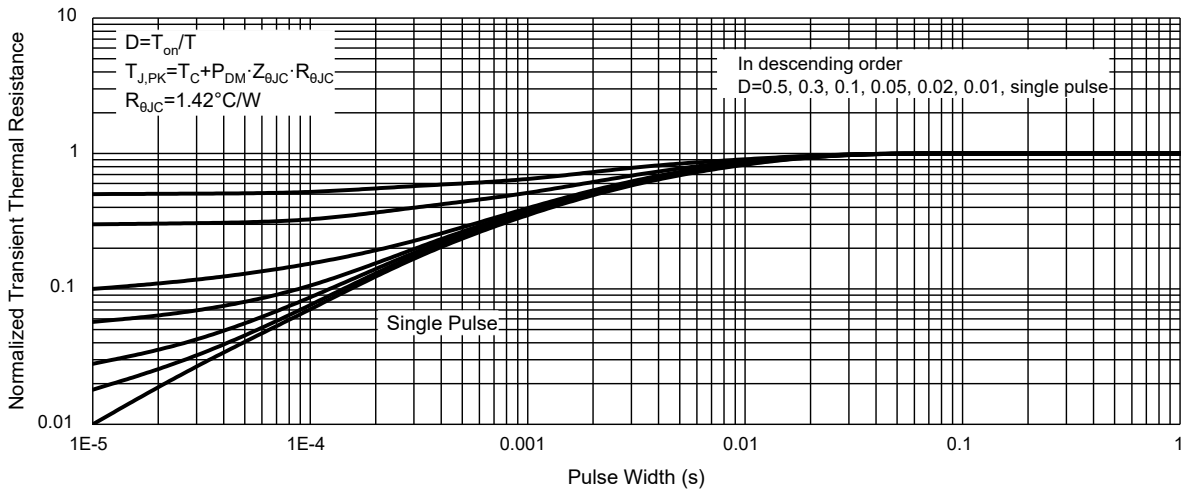


Fig. 8 - Normalized Maximum Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 5Kpcs/Reel

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